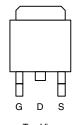


Vishay Siliconix

N-Channel 150 V (D-S) 175 °C MOSFET

PRODUCT SUMMARY			
V _{DS} (V)	R _{DS(on)} (Ω)	I _D (A)	
150	0.073 at V _{GS} = 10 V	23	
	0.077 at V _{GS} = 6 V	22.5	

TO-263



Top View

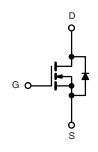
Ordering Information: SUM23N15-73-E3 (Lead (Pb) free)

FEATURES

- TrenchFET[®] Power MOSFETS
- 175 °C Junction Temperature
- Low Thermal Resistance Package
- PWM Optimized
- Compliant to RoHS Directive 2002/95/EC

APPLICATIONS

• Primary Side Switch



N-Channel MOSFET

ABSOLUTE MAXIMUM RATING	S (T _C = 25 °C, unless of	herwise noted)		
Parameter	Symbol	Limit	Unit	
Drain-Source Voltage	V _{DS}	150	v	
Gate-Source Voltage	V _{GS}	± 20		
Continuous Drain Current (T ₁ = 175 °C)	T _C = 25 °C	L	23	
	T _C = 125 °C	I _D	13.4	
Pulsed Drain Current	I _{DM}	35	— A	
Avalanche Current	I _{AR}	25		
Repetitive Avalanche Energy ^a	L = 0.1 mH	E _{AR}	31	mJ
	T _C = 25 °C	Р	100 ^b	
Maximum Power Dissipation ^a	T _A = 25 °C ^c		3.75	W
Operating Junction and Storage Temperature Range		T _J , T _{stg}	- 55 to 175	°C

THERMAL RESISTANCE RATINGS				
Parameter	Symbol	Limit	Unit	
Junction-to-Ambient (PCB Mount) ^c	R _{thJA}	40	°C/W	
Junction-to-Case (Drain)	R _{thJC}	1.5	0/10	

Notes:

a. Duty cycle \leq 1 %.

b. See SOA curve for voltage derating.

c. When mounted on 1" square PCB (FR-4 material).

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Parameter	Symbol	Test Conditions	Min.	Тур.	Max.	Unit
Static				•		
Drain-Source Breakdown Voltage	V _{DS}	$V_{GS} = 0 V$, $I_{D} = 250 \mu A$	150			v
Gate-Threshold Voltage	V _{GS(th)}	$V_{DS} = V_{GS}, I_D = 250 \ \mu A$	2		4	
Gate-Body Leakage	I _{GSS}	$V_{DS} = 0 V, V_{GS} = \pm 20 V$			± 100	nA
Zero Gate Voltage Drain Current		V _{DS} = 120 V, V _{GS} = 0 V			1	μΑ
	I _{DSS}	V_{DS} = 120 V, V_{GS} = 0 V, T_{J} = 125 °C			50	
		$V_{DS} = 120 \text{ V}, \text{ V}_{GS} = 0 \text{ V}, \text{ T}_{\text{J}} = 175 ^{\circ}\text{C}$			250	
On-State Drain Current ^a	I _{D(on)}	$V_{DS} \ge 5 \text{ V}, \text{ V}_{GS} = 10 \text{ V}$	35			Α
		V _{GS} = 10 V, I _D = 15 A		0.059	0.073	- Ω
Drain-Source On-State Resistance ^a		V_{GS} = 10 V, I_{D} = 15 A, T_{J} = 125 °C			0.140	
	R _{DS(on)}	V_{GS} = 10 V, I_{D} = 15 A, T_{J} = 175 °C			0.168	
		V _{GS} = 6 V, I _D = 10 A		0.062	0.077	
Forward Transconductance ^a	9 _{fs}	V _{DS} = 15 V, I _D = 25 A	10			S
Dynamic ^b	•			•		
Input Capacitance	C _{iss}	V _{GS} = 0 V, V _{DS} = 25 V, f = 1 MHz		1290		pF
Output Capacitance	C _{oss}			160		
Reverse Transfer Capacitance	C _{rss}			70		
Total Gate Charge ^c	Qg			22	35	nC
Gate-Source Charge ^c	Q _{gs}	$V_{DS} = 75 \text{ V}, V_{GS} = 10 \text{ V}, I_{D} = 23 \text{ A}$		6		
Gate-Drain Charge ^c	Q _{gd}			7.5		
Gate Resistance	R _G			4		Ω
Turn-On Delay Time ^c	t _{d(on)}			10	15	
Rise Time ^c	t _r	V_{DD} = 75 V, R _L = 3.26 Ω I _D \cong 23 A, V _{GEN} = 10 V, R _G = 2.5 Ω		60	90	- ns
Turn-Off Delay Time ^c	t _{d(off)}			30	43	
Fall Time ^c	t _f			45	70	
Source-Drain Diode Ratings and Cha	racteristics (1	_C = 25 °C) ^b				
Continuous Current	۱ _S				35	^
Pulsed Current	I _{SM}				23	A
Forward Voltage ^a	V _{SD}	$I_{F} = 23 \text{ A}, \text{ V}_{GS} = 0 \text{ V}$		1	1.5	V
Reverse Recovery Time	t _{rr}			100	150	ns
Peak Reverse Recovery Charge	I _{RM(REC)}	I _F = 23 A, dl/dt = 100 A/μs		5	8	А
Reverse Recovery Charge	Q _{rr}			0.25	0.6	μC

Notes:

a. Pulse test; pulse width \leq 300 $\mu s,$ duty cycle \leq 2 %.

b. Guaranteed by design, not subject to production testing.

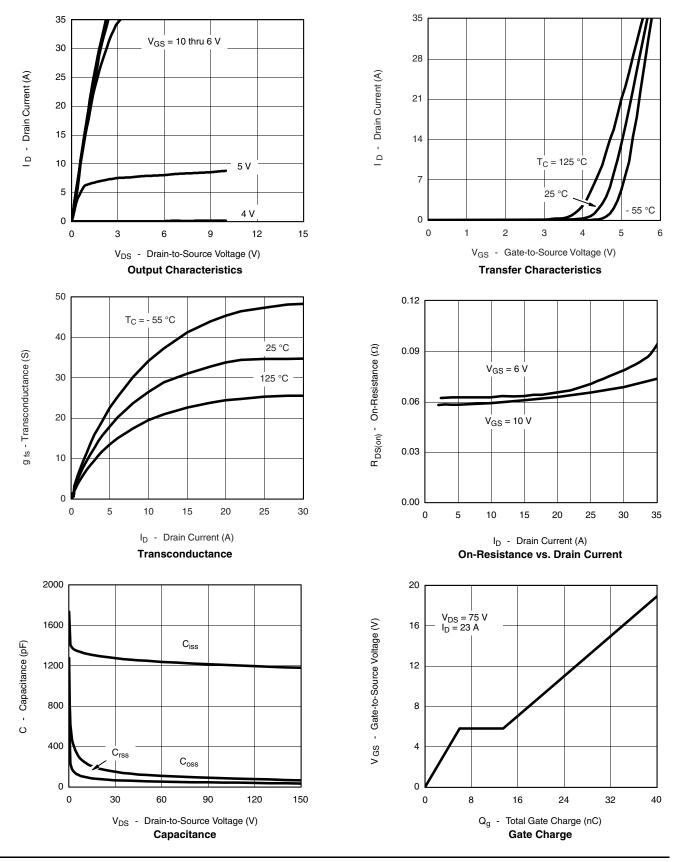
c. Independent of operating temperature.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.



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TYPICAL CHARACTERISTICS (25 °C unless noted)

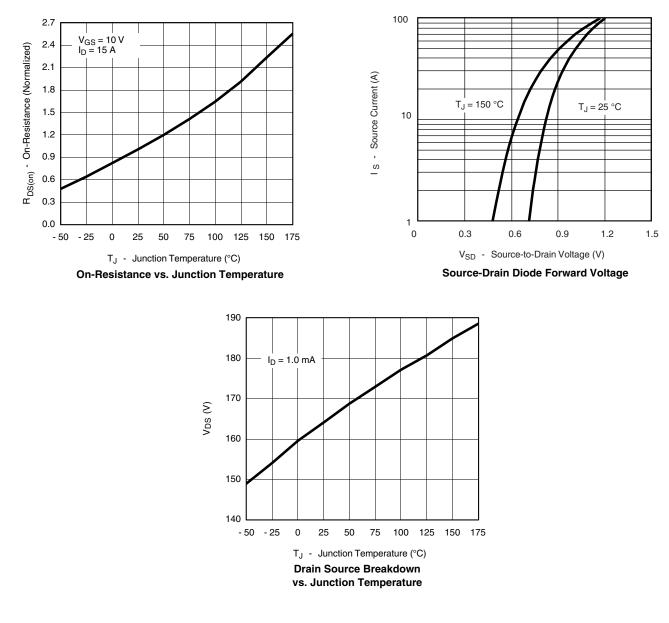


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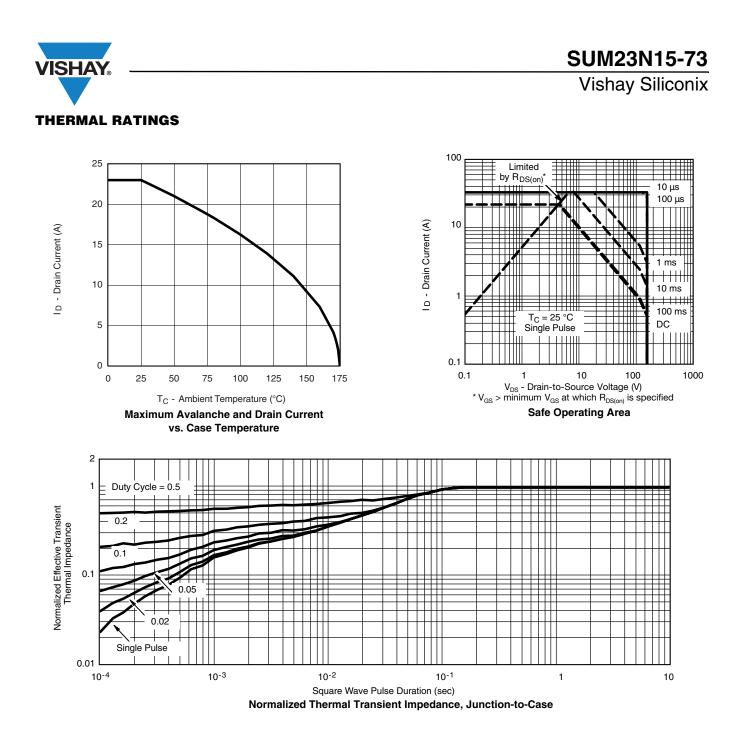
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TYPICAL CHARACTERISTICS (25 °C unless noted)



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